D44H Series (NPN), **D45H Series (PNP)**

Complementary Silicon Power Transistors

These series of plastic, silicon NPN and PNP power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Low Collector-Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage D44H8, D45H8 D44H11, D45H11	V _{CEO}	60 80	Vdc
Emitter Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	I _C	10	Adc
Collector Current – Peak (Note 1)	I _{CM}	20	Adc
Total Power Dissipation @ T _C = 25°C @ T _A = 25°C	P _D	70 2.0	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Width ≤ 6.0 ms, Duty Cycle ≤ 50%

THERMAL CHARACTERISTICS

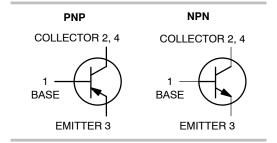
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.8	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T _L	275	°C

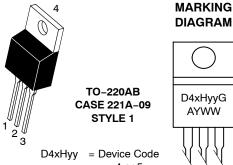


ON Semiconductor®

http://onsemi.com

10 AMP COMPLEMENTARY SILICON POWER TRANSISTORS 60, 80 VOLTS





x = 4 or 5

yy = 8 or 11

= Assembly Location

WW = Work Week = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
D44H8G	TO-220 (Pb-Free)	50 Units/Rail
D44H11G	TO-220 (Pb-Free)	50 Units/Rail
D45H8G	TO-220 (Pb-Free)	50 Units/Rail
D45H11G	TO-220 (Pb-Free)	50 Units/Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		l.		l		
Collector–Emitter Sustaining Voltage (I _C = 30 mAdc, I _B = 0 Adc)	D44H8, D45H8 D44H11, D45H11	V _{CEO(sus)}	60 80	- -	- -	Vdc
Collector Cutoff Current (V _{CE} = Rated V _{CEO} , V _{BE}	= 0)	I _{CES}	-	-	10	μΑ
Emitter Cutoff Current (V _{EB} = 5.0 Vdc)		I _{EBO}	-	_	10	μΑ
ON CHARACTERISTICS		<u>.</u>				*
DC Current Gain $ (V_{CE} = 1.0 \text{ Vdc}, I_{C} = 2.0 \text{ Adc}) $ $ (V_{CE} = 1.0 \text{ Vdc}, I_{C} = 4.0 \text{ Adc}) $		h _{FE}	60 40	- -	- -	-
Collector–Emitter Saturation Voltage (I _C = 8.0 Adc, I _B = 0.4 Adc)		V _{CE(sat)}	-	-	1.0	Vdc
Base-Emitter Saturation Voltage (I _C = 8.0 Adc, I _B = 0.8 Adc)		V _{BE(sat)}	-	-	1.5	Vdc
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V _{CB} = 10 Vdc, f _{test} = 1.0 MHz)	D44H Series D45H Series	C _{cb}	<u>-</u> -	90 160	<u>-</u>	pF
Gain Bandwidth Product (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 20 MHz)	D44H Series D45H Series	f _T	<u>-</u> -	50 40	<u>-</u>	MHz
SWITCHING TIMES						
Delay and Rise Times (I _C = 5.0 Adc, I _{B1} = 0.5 Adc)	D44H Series D45H Series	t _d + t _r	- -	300 135	- -	ns
Storage Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ Adc})$	D44H Series D45H Series	t _s	- -	500 500	- -	ns
Fall Time (I _C = 5.0 Adc, I _{B1} = 102 = 0.5 Adc)	D44H Series D45H Series	t _f	- -	140 100	- -	ns

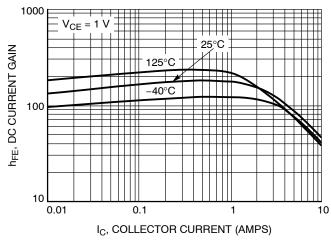


Figure 1. D44H11 DC Current Gain

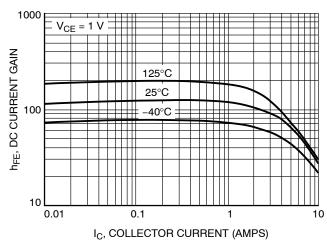


Figure 2. D45H11 DC Current Gain

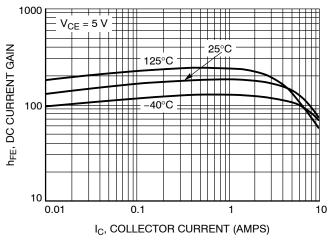


Figure 3. D44H11 DC Current Gain

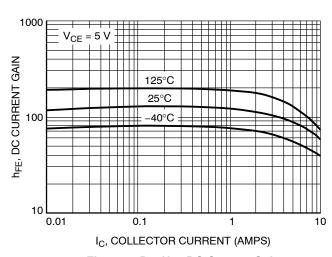


Figure 4. D45H11 DC Current Gain

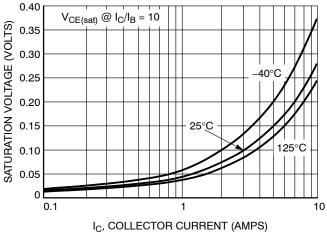


Figure 5. D44H11 ON-Voltage

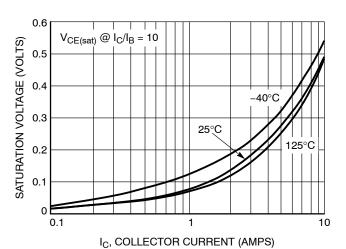
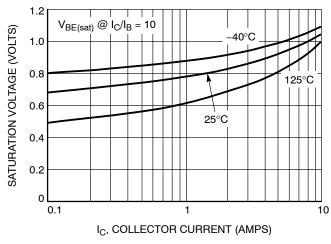


Figure 6. D45H11 ON-Voltage



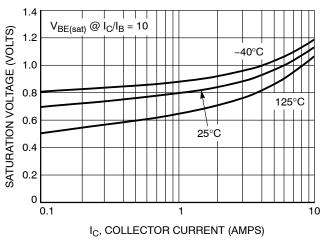
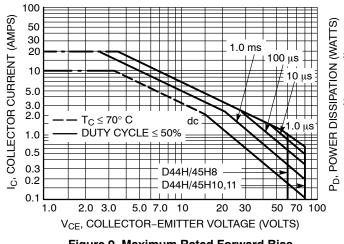


Figure 7. D44H11 ON-Voltage

Figure 8. D45H11 ON-Voltage



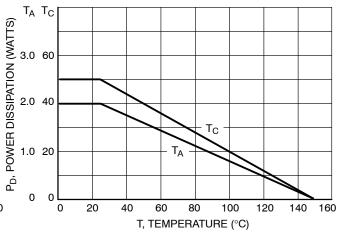


Figure 9. Maximum Rated Forward Bias Safe Operating Area

Figure 10. Power Derating

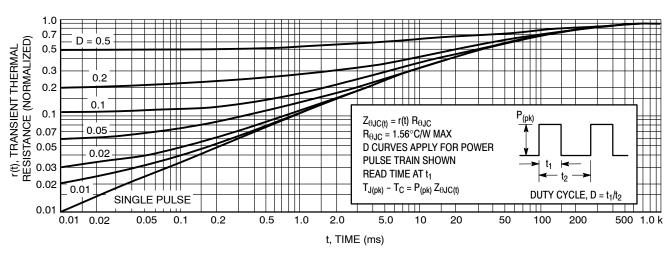
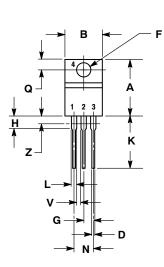
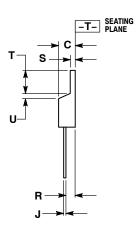


Figure 11. Thermal Response

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AG





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

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